

1-Line Bi-directional TVS Diode

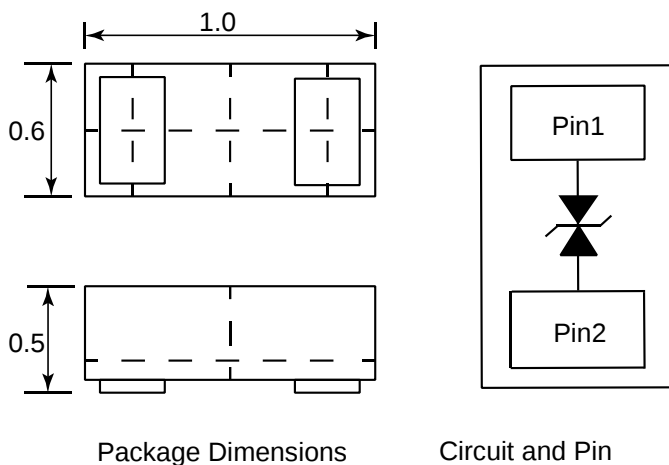
Description

The PESDU1261P1 is a 12V bi-directional TVS diode, to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU1261P1 complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small lead-free DFN1006-2 package. The small size and high ESD protection make PESDU1261P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Operating voltage: 12V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 7A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



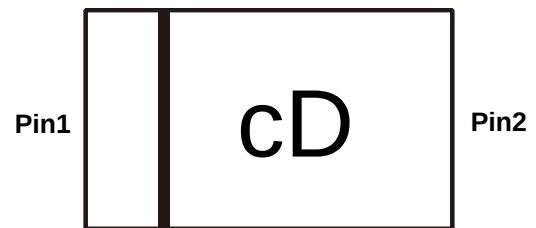
Mechanical Characteristics

- Package: DFN1006-2 (1.0×0.6×0.5mm)
- Case Material: "Green" Molding Compound.
- Moisture Sensitivity: Level 1 per J-STD-020
- Marking Information: See Below

Applications

- Cellular Handsets & Accessories
- Personal Digital Assistants
- Notebooks & Handhelds
- Portable Instrumentation
- Digital Cameras

Marking Information



cD = Device Marking Code

Ordering Information

Part Number	Shipping	Reel Size
PESDU1261P1	10000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P_{PK}	100	W
Peak Pulse Current (8/20 μs)	I_{PP}	7	A
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Lead temperature	T_L	260	$^{\circ}\text{C}$
Junction Temperature	T_J	125	$^{\circ}\text{C}$
Operating Temperature Range	T_{OP}	$-40 \sim +125$	$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			12	V	
Breakdown Voltage	V_{BR}	13.8	15.5		V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_R			0.1	μA	$V_{RWM} = 12\text{V}$
Clamping voltage ¹⁾	V_{CL}		22.0		V	$I_{PP} = 16\text{A}$, $t_p = 100\text{ns}$
Dynamic resistance ¹⁾	R_{DYN}		0.35		Ω	
Clamping voltage ²⁾	V_{CL}		22.0		V	$V_{ESD} = 8\text{kV}$
Clamping Voltage ³⁾	V_C		16	17	V	$I_{PP} = 1\text{A}$ (8/20 μs pulse)
Clamping Voltage ³⁾	V_C		20	25	V	$I_{PP} = 7\text{A}$ (8/20 μs pulse)
Junction Capacitance	C_J		12		pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$

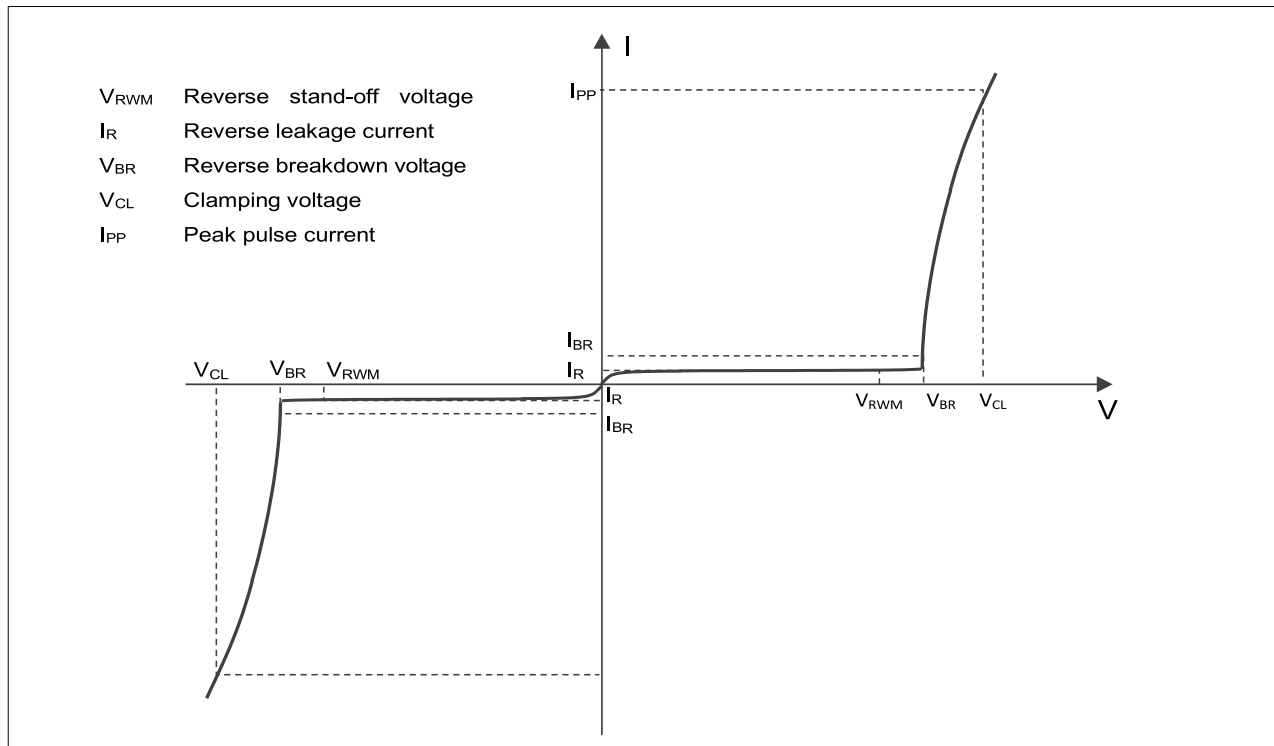
Notes:

1) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100\text{ns}$, $t_r = 2\text{ns}$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

2) Contact discharge mode, according to IEC61000-4-2.

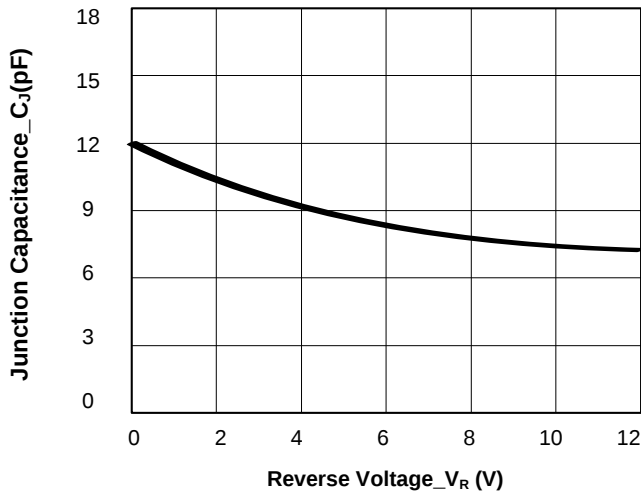
3) Non-repetitive current pulse, according to IEC61000-4-5.

Electrical characteristics ($T_A = 25^\circ\text{C}$, unless otherwise noted)

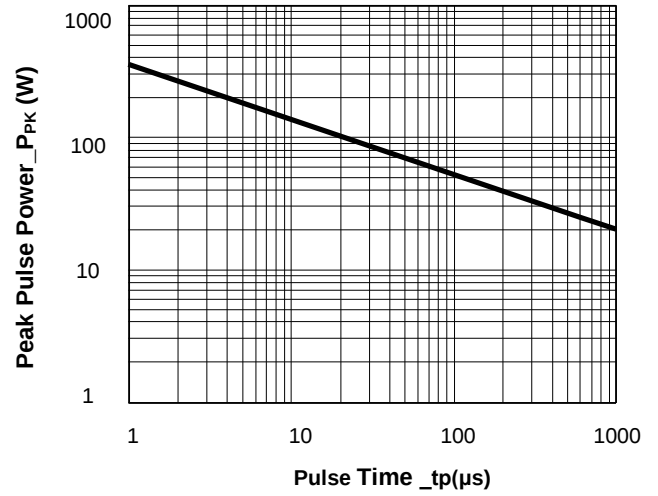


Definitions of electrical characteristics

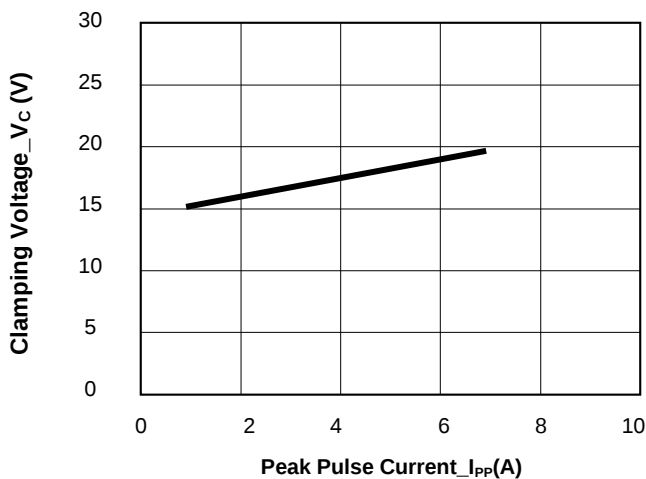
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



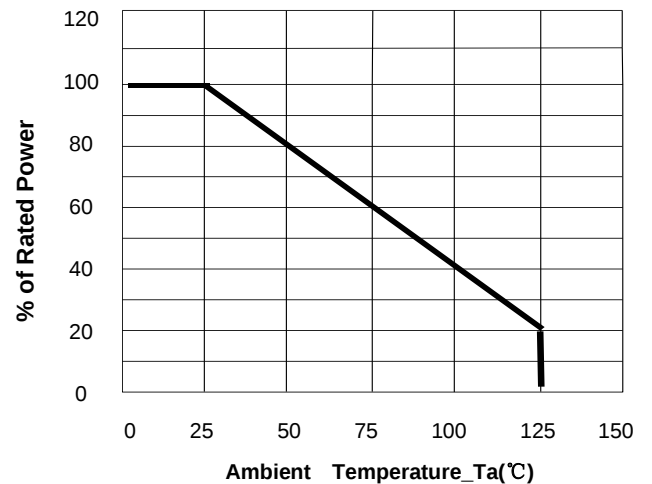
Junction Capacitance vs. Reverse Voltage



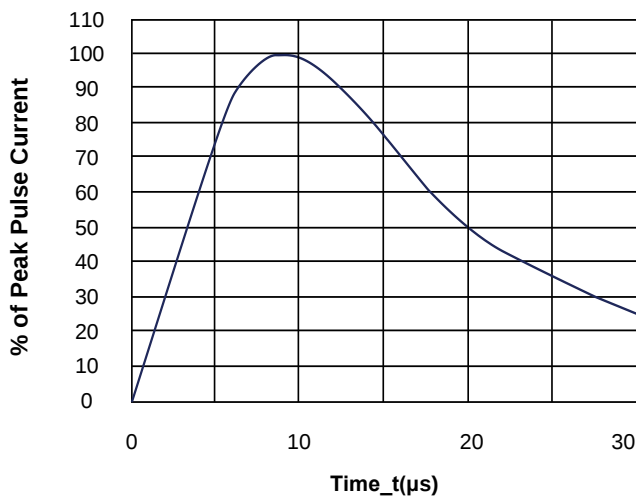
Peak Pulse Power vs. Pulse Time



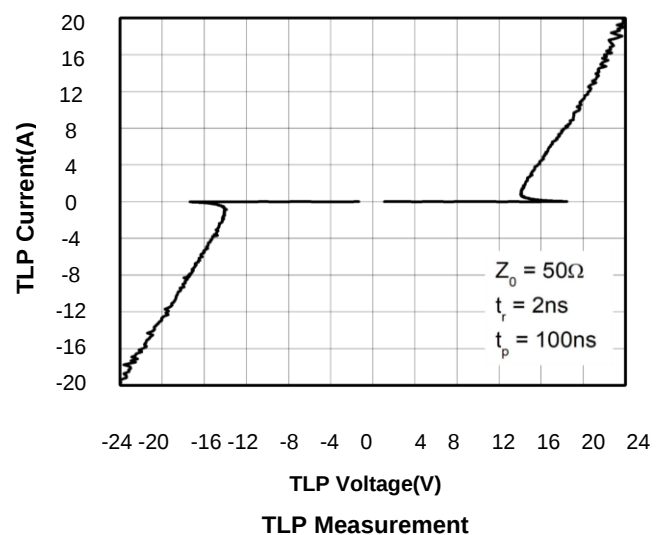
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve

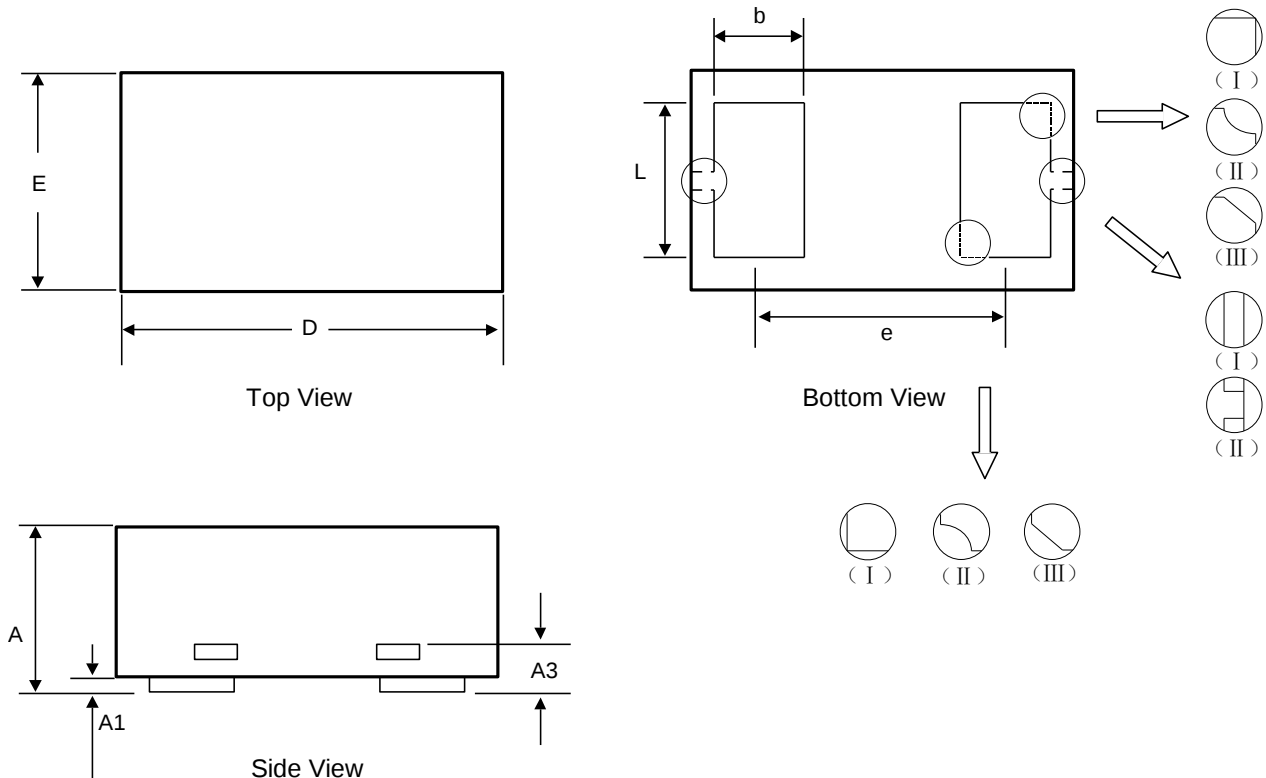


8/20 μs Pulse Waveform



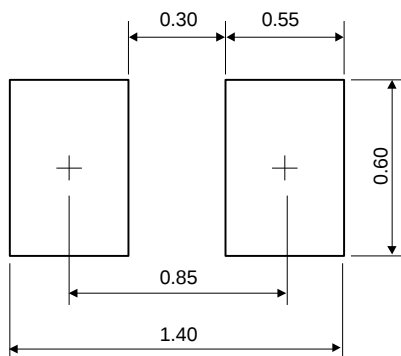
TLP Measurement

DFN1006-2 Package Outline Drawing



Symbol	Dimensions in Millimeters		
	Min.	Typ.	Max.
A	0.340	0.450	0.550
A1	0.000	0.020	0.050
A3	0.125 Ref.		
D	0.950	1.000	1.075
E	0.490	0.600	0.675
b	0.200	0.250	0.300
L	0.450	0.500	0.550
e	0.650 BSC		

Recommended PCB Layout (Unit: mm)

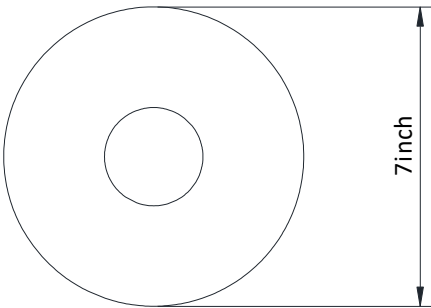


Notes:

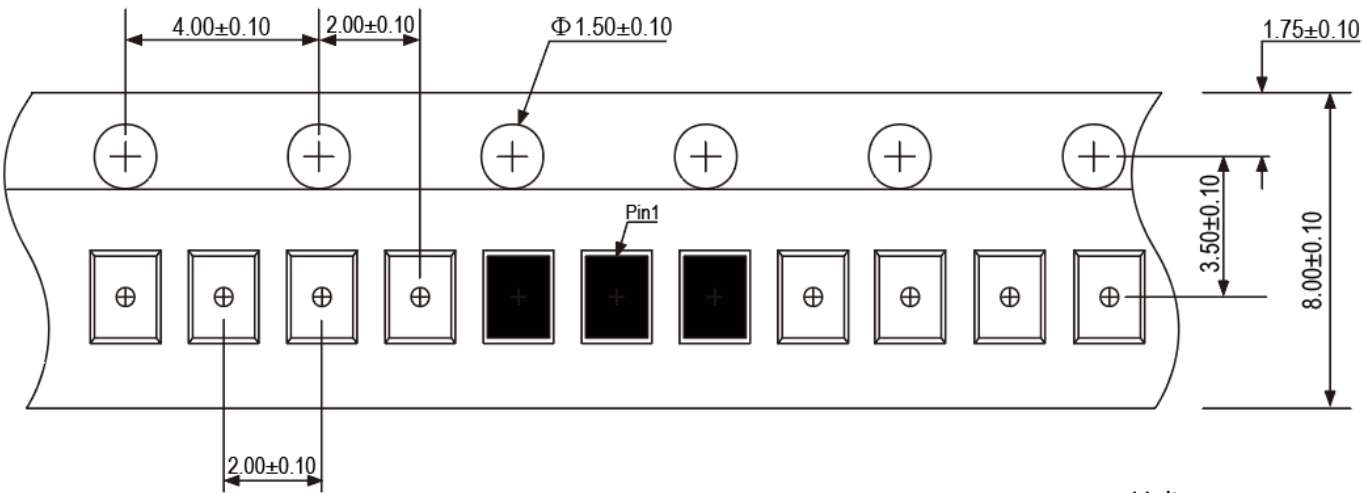
This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

TAPE AND REEL INFORMATION

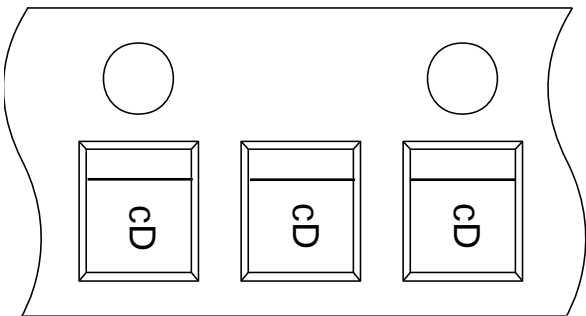
Reel Dimensions



Tape Dimensions



Unit:mm



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